DS05-11127-1E

MEMORY Unbuffered 2 M × 64 BIT SYNCHRONOUS DYNAMIC RAM DIMM

MB8502S064AG-100/-84/-67

168-pin, 4 Clock, 1-bank, based on 2 M × 8 Bit SDRAMs with SPD

DESCRIPTION

The Fujitsu MB8502S064AG is a fully decoded, CMOS Synchronous Dynamic Random Access Memory (SDRAM) Module consisting of eight MB81117822E devices which organized as two banks of 2 M \times 8 bits and a 2K-bit serial EEPROM on a 168-pin glass-epoxy substrate.

The MB8502S064AG features a fully synchronous operation referenced to a positive edge clock whereby all operations are synchronized at a clock input which enables high performance and simple user interface coexistence.

The MB8502S064AG is optimized for those applications requiring high speed, high performance and large memory storage, and high density memory organizations.

This module is ideally suited for workstations, PCs, laser printers, and other applications where a simple interface is needed.

■ PRODUCT LINE & FEATURES

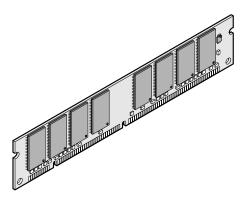
Para	ameter	MB8502S064AG-100	MB8502S064AG-84	MB8502S064AG-67		
Clock Frequency		100 MHz max.	84 MHz max.	67 MHz max.		
Burst Mode Cycle Time		10 ns max. (CL = 3) 15 ns max. (CL = 2)	12 ns max. (CL = 3) 17 ns max. (CL = 2)	15 ns max. (CL = 3) 20 ns max. (CL = 2)		
RAS Access Time		54 ns max.	56 ns max.	60 ns max.		
CAS Access Time)	24 ns max.	24 ns max. 26 ns max.			
Output Valid from	Output Valid from Clock		8.5 ns max. (CL = 3) 9 ns max. (CL = 2)	9 ns max. (CL = 3) 10 ns max. (CL = 2)		
Power	Burst Mode	3888 mW max. 3600 mW max.		3312 mW max.		
Dissipation	Power Down Mode	57.6 mW max.				

- Unbuffered 168-pin DIMM Socket Type (Lead pitch: 1.27 mm)
- Conformed to JEDEC Standard (4 CLK)
- Organization: 2,097,152 words × 64 bits
- Memory: MB81117822A (2 M × 8, 2-bank) × 8 pcs.
- 3.3 V ±0.3 V Supply Voltage
- All input/output LVTTL compatible

- 2048 Refresh Cycle every 32.8 ms
- Auto and Self Refresh
- CKE Power Down Mode
- DQM Byte Masking (Read/Write)
- Serial Presence Detect (SPD) with Serial EEPROM: JEDEC Standard SPD Format
- Module size:
 1.0" (height) × 5.25" (length) × 0.157" (thickness)

■ PACKAGE





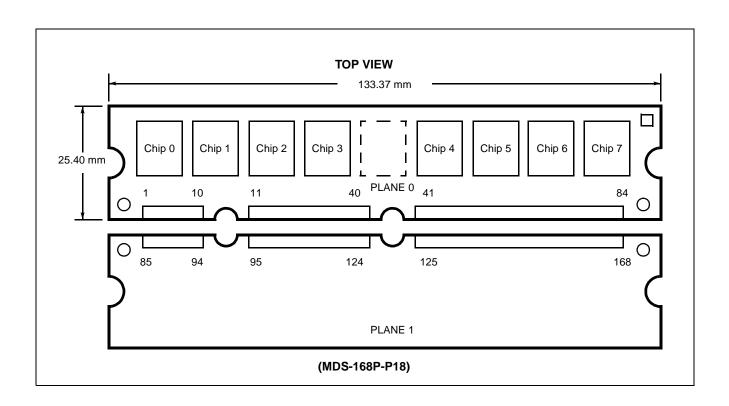
(MDS-168P-P18)

Package and Ordering Information

- 168-pin DIMM, order as MB8502S064AG-xxDG (DG = Gold Pad)

■ PIN ASSIGNMENTS

Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name
1	Vss	29	DQMB ₁	57	DQ18	85	Vss	113	DQMB ₅	141	DQ ₅₀
2	DQ₀	30	CS ₀	58	DQ ₁₉	86	DQ ₃₂	114	N.C.	142	DQ ₅₁
3	DQ ₁	31	N.C.	59	Vcc	87	DQ ₃₃	115	RAS	143	Vcc
4	DQ ₂	32	Vss	60	DQ ₂₀	88	DQ ₃₄	116	Vss	144	DQ52
5	DQ₃	33	A ₀	61	N.C.	89	DQ ₃₅	117	A ₁	145	N.C.
6	Vcc	34	A 2	62	N.C.	90	Vcc	118	Аз	146	N.C.
7	DQ4	35	A 4	63	N.C.	91	DQ36	119	A 5	147	N.C.
8	DQ ₅	36	A 6	64	Vss	92	DQ ₃₇	120	A ₇	148	Vss
9	DQ ₆	37	A 8	65	DQ ₂₁	93	DQ38	121	A 9	149	DQ53
10	DQ ₇	38	A ₁₀	66	DQ ₂₂	94	DQ ₃₉	122	BA ₀	150	DQ ₅₄
11	DQ ₈	39	N.C.	67	DQ ₂₃	95	DQ ₄₀	123	N.C.	151	DQ ₅₅
12	Vss	40	Vcc	68	Vss	96	Vss	124	Vcc	152	Vss
13	DQ ₉	41	Vcc	69	DQ ₂₄	97	DQ ₄₁	125	CLK ₁	153	DQ ₅₆
14	DQ ₁₀	42	CLK ₀	70	DQ ₂₅	98	DQ ₄₂	126	N.C.	154	DQ ₅₇
15	DQ11	43	Vss	71	DQ ₂₆	99	DQ43	127	Vss	155	DQ58
16	DQ ₁₂	44	N.C.	72	DQ ₂₇	100	DQ ₄₄	128	CKE ₀	156	DQ ₅₉
17	DQ ₁₃	45	CS ₂	73	Vcc	101	DQ ₄₅	129	N.C.	157	Vcc
18	Vcc	46	DQMB ₂	74	DQ ₂₈	102	Vcc	130	DQMB ₆	158	DQ ₆₀
19	DQ ₁₄	47	DQMB ₃	75	DQ29	103	DQ ₄₆	131	DQMB7	159	DQ ₆₁
20	DQ ₁₅	48	N.C.	76	DQ ₃₀	104	DQ ₄₇	132	N.C.	160	DQ ₆₂
21	N.C.	49	Vcc	77	DQ ₃₁	105	N.C.	133	Vcc	161	DQ ₆₃
22	N.C.	50	N.C.	78	Vss	106	N.C.	134	N.C.	162	Vss
23	Vss	51	N.C.	79	CLK ₂	107	Vss	135	N.C.	163	CLK ₃
24	N.C.	52	N.C.	80	N.C.	108	N.C.	136	N.C.	164	N.C.
25	N.C.	53	N.C.	81	N.C.	109	N.C.	137	N.C.	165	SA ₀
26	Vcc	54	Vss	82	SDA	110	Vcc	138	Vss	166	SA ₁
27	WE	55	DQ ₁₆	83	SCL	111	CAS	139	DQ ₄₈	167	SA ₂
28	DQMB ₀	56	DQ ₁₇	84	Vcc	112	DQMB ₄	140	DQ49	168	Vcc



■ PIN DESCRIPTIONS

Symbol	1/0	Function	Symbol	I/O	Function
A ₀ to A ₁₀ , BA ₀	ı	Address Input	DQ ₀ to DQ ₆₃	I/O	Data Input/Data Output
RAS	I	Row Address Strobe	Vcc	_	Power Supply (+3.3 V)
CAS	ı	Column Address Strobe	Vss	_	Ground (0 V)
WE	I	Write Enable	N.C.	_	No Connection
DQMB ₀ to DQMB ₇	I	Data (DQ) Mask	SA ₀ to SA ₂	I	Serial PD Address Input
CLK₀ to CLK₃	I	Clock Input	SCL	I	Serial PD Clock
CKE₀	I	Clock Enable	SDA	I/O	Serial PD Address/Data Input/Output
CS ₀ , CS ₂	I	Chip Select			

■ SERIAL-PD INFORMATION

Byte	Function Described		ı	Hex Value	;
Буге	FullCuoli Described		-100	-84	-67
0	Defines Number of Bytes Written into	128 Byte	80h	80h	80h
	Serial Memory at Module Manufacture				
1	Total Number of Bytes of SPD Memory Device	256 Byte	08h	08h	08h
2	Fundamental Memory Type	SDRAM	04h	04h	04h
3	Number of Row Addresses	11	0Bh	0Bh	0Bh
4	Number of Column Addresses	9	09h	09h	09h
5	Number of Module Banks	1 bank	01h	01h	01h
6	Data Width	64 bit	40h	40h	40h
7	Data Width (Continuation)	+0	00h	00h	00h
8	Interface Type	LVTTL	01h	01h	01h
9	SDRAM Cycle Time (Highest CAS Latency)	10/12/15 ns	A0h	C0h	F0h
10	SDRAM Access from Clock (Highest CAS Latency)	8.5/8.5/9 ns	85h	85h	90h
11	DIMM Configuration Type	Non-Parity	00h	00h	00h
12	Refresh Rate/Type	Self, Normal	80h	80h	80h
13	Primary SDRAM Width	×8	08h	08h	08h
14	Error Checking SDRAM Width	0	00h	00h	00h
15	Minimum Clock Delay for Back to Back Random Column	1 Cycle	01h	01h	01h
	Addresses				
16	Burst Lengths Supported	1, 2, 4, 8, Page	8Fh	8Fh	8Fh
17	Number of Banks on Each SDRAM Device	2 bank	02h	02h	02h
18	CAS Latency	2, 3	06h	06h	06h
19	CS Latency	0	01h	01h	01h
20	Write Latency	0	01h	01h	01h
21	SDRAM Module Attributes	UN-buffer	00h	00h	00h
22	SDRAM Device Attributes	*1	06h	06h	06h
23	SDRAM Cycle Time (2nd. Highest CAS Latency)	15/17/20 ns	F0h	20h	FFh
24	SDRAM Access from Clock (2nd. Highest CAS Latency)	9/9/10 ns	90h	90h	A0h
25	SDRAM Cycle Time (3rd. Highest CAS Latency)	No Support	00h	00h	00h
26	SDRAM Access from Clock (3rd. Highest CAS Latency)	No Support	00h	00h	00h
27	Minimum Row Precharge Time (t _{RP})	30/35/40 ns	1Eh	23h	28h
28	Row Activate to Row Activate Min. (trrd)	30/30/30 ns	1Eh	1Eh	1Eh
29	RAS to CAS Delay Min. (trcd)	30/30/30 ns	1Eh	1Eh	1Eh
30	Minimum RAS Pulse Width	60/65/70 ns	3Ch	41h	46h
31	Module Bank Density	16 MByte	04h	04h	04h
32 to 61	Unused Storage Locations	_	00h	00h	00h
62	SPD Data Revision Code	1	01h	01h	01h
63	Checksum for Byte 0 to 62	*2	4Ah	A4h	D8h
64 to 98	Manufacturer's Information: Unused Storage	_	00h	00h	00h
99 to 127	Vendor Specific Data: Unused Storage	_	00h	00h	00h
128+	Unused Storage Locations	_	_	_	_

Note: Any write operation must NOT be executed into the addresses of Byte 0 to Byte 127. Some or all data stored into Byte 0 to Byte 127 may be broken.

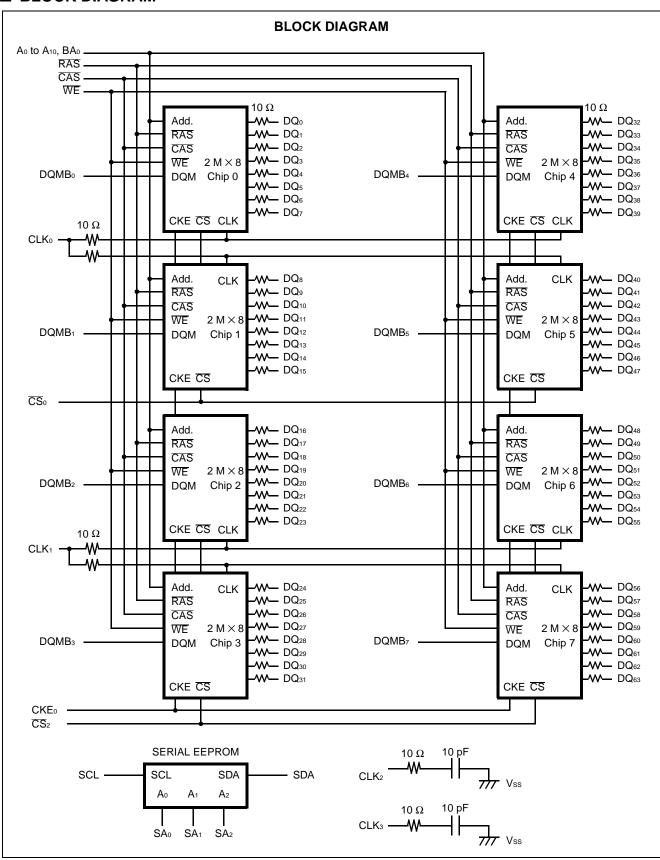
*1. Byte 22: SDRAM Device Attributes

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
TBD	TBD	Upper Vcc tolerance	Lower Vcc tolerance	Supports Write 1 /Read Burst	Supports Precharge All	Supports Auto- precharge	Supports Early RAS Precharge
0	0	0	0	0	1	1	0

^{*2.} Byte 63: Checksum for Bytes 0 to 62

This byte is the checksum for bytes 0 through 62. This byte contains the value of the low 8-bits of the arithmetic sum of bytes 0 through 62.

■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Parameter	Symbol	Va	Unit	
Farameter	Symbol	Min.	Max.	Offic
Supply Voltage*	Vcc	-0.5	+4.6	V
Input Voltage*	Vin	-0.5	+4.6	V
Output Voltage*	Vоит	-0.5	+4.6	V
Storage Temperature	Тѕтѕ	– 55	+125	°C
Power Dissipation	Po	_	10.4	W
Output Current (D.C.)	Іоит	-50	+50	mA

^{*:} Voltages referenced to Vss (= 0 V)

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Desembles	Notes	Symbol		l lmi4		
Parameter	Notes		Min.	Тур.	Max.	Unit
Supply Voltage	*4	Vcc	3.0	3.3	3.6	V
Supply Voltage	Ī	Vss	0	0	0	V
Input High Voltage, All Inputs	*1, 2	ViH	2.0	_	Vcc +0.5	V
Input Low Voltage, All Inputs	*1, 3	Vıl	-0.5	_	0.8	V
Ambient Temperature		TA	0	_	+70	°C

^{*1.} Voltages referenced to Vss (= 0 V)

WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

^{*2.} Overshoot limit: V_{IH} (max.) = V_{CC} +1.5 V with a pulsewidth ≤ 5 ns.

^{*3.} Undershoot limit: V_{\parallel} (min.) = -1.5 V with a pulsewidth ≤ 5 ns.

■ CAPACITANCE

 $(Vcc = +3.3 \text{ V}, f = 1 \text{ MHz}, T_A = +25^{\circ}\text{C})$

Paramet	or.	Symbol	Va	lue	Unit
Paramet	ei	Symbol	Min.	Max.	Offic
	Ao to A10, BA0	C _{IN1}	_	40	pF
	RAS, CAS, WE	CIN2	_	37	pF
	CS ₀ , CS ₂	Сімз	_	21	pF
Input Conscitones	CKE ₀	CIN4	_	40	pF
Input Capacitance	CLK ₀ to CLK ₃	CIN5	_	30	pF
	DQMB ₀ to DQMB ₇	C _{IN6}	_	11	pF
	SCL	Cscl	_	6	pF
	SA ₀ , SA ₁ , SA ₂	Csa	_	8	pF
Input/Output Canacitanes	SDA	CSDA	_	7	pF
Input/Output Capacitance	DQo to DQ63	Сра	_	12	pF

■ DC CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

Donomotor No	.4		Cumbal	Condition	Va	lue	1110:4
Parameter No	otes		Symbol	Condition	Min.	Max.	Unit
		MB8502S064AG-100		No Burst;		680	mA
		MB8502S064AG-84	Icc1s	tck = min trc = min	_	640	mA
Operating Current	*1	MB8502S064AG-67		One Bank Active		600	mA
(Average Power Supply Current)	1	MB8502S064AG-100		No Burst;	Min. Max.	mA	
		MB8502S064AG-84	Icc1D	tck = min trc = min	_	960	mA
		MB8502S064AG-67		All Banks Active		880	mA
Precharge Standby Current (Power	*1		Ісс2Р	CKE = VIL, tck = min All Banks Idle	_	16	mA
Supply Current)	ı		Ісс2N	CKE = Vін, tcк = min All Banks Idle	_	240	mA
Active Standby Current (Power	*1		Іссзр	CKE = V _{IL} , t _{CK} = min Any Bank Active	_	240	mA
Supply Current)	1		Іссзи	CKE = V _{IH} , tck = min Any Bank Active	_	400	mA
Burst Mode Current	*1	MB8502S064AG-100				1080	mA
(Average Power		MB8502S064AG-84	Icc4	tcк = min	_	1000	mA
Supply Current)		MB8502S064AG-67			_	680 640 600 1040 960 880 16 240 400 1080 1000 920 880 800 720 16 50	mA
Auto-refresh Current		MB8502S064AG-100		Auto Refresh	_	880	mA
(Average Power	*1	MB8502S064AG-84	Icc5	tck = min trc = min	_	- 640 600 1040 960 880 - 16 - 240 - 400 - 1080 - 1000 - 920 - 880 - 720 - 16 0 50	mA
Supply Current)		MB8502S064AG-67		trrd = min		Max. 680 640 600 1040 960 880 240 400 1080 1000 920 880 720 16 50	mA
Self-refresh Current (Average Power Supply C	Curre	nt)	Icc6	CKE = VIL	_	16	mA
Input Leakage Current (A	dl Inp	outs)	lı (L)	$0 \text{ V} \le \text{V}_{\text{IN}} \le \text{V}_{\text{CC}}$ All other pins not under test = 0 V $3.0 \text{ V} \le \text{V}_{\text{CC}} \le 3.6 \text{ V}$	-50	50	μΑ
Output Leakage Current			lo(L)	Output is disabled (Hi-Z) $0 \text{ V} \leq \text{Vout} \leq \text{Vcc}$ $3.0 \text{ V} \leq \text{Vcc} \leq 3.6 \text{ V}$	-10	10	μΑ
LVTTL Output High Voltage	*2		Vон	lон = −2.0 mA	2.4	_	V
LVTTL Output Low Voltage	*2		Vol	lo _L = +2.0 mA	_	0.4	V

- Notes: *1. lcc depends on the output termination, load conditions, clock cycle rate and signal clock rate. The specified values are obtained with the output open and no termination register.
 - *2. Voltages referenced to Vss (= 0 V)
 - *3. An initial pause (DESL on NOP) of 200 µs is required after power-on followed by a minimum of eight Auto-refresh cycles.
 - *4. DC characteristics is the Serial PD standby state (V_{IN} = GND or V_{CC}).

■ AC CHARACTERISTICS

(1) BASE CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

No.	Parameter Notes		Symbol		S064AG 00	MB8502S064AG -84		MB8502S064AG -67		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
1	Clock Period	CL = 3	t ск	10	_	12	_	15	_	ns
'	Clock Period	CL = 2	lCK -	15	_	17	_	20	_	ns
2	Clock High Time		t cH	4	_	4		4	_	ns
3	Clock Low Time		t cL	4	_	4	_	4	_	ns
4	CS Setup Time		t sc	3	_	3	_	3	_	ns
5	CS Hold Time		t HC	1	_	1		1	_	ns
6	Input Setup Time		t sı	3	_	3	_	3	_	ns
7	Input Hold Time		tнı	1	_	1	_	1	_	ns
8	Data Input Setup Time		tsid	3	_	3	_	3	_	ns
9	Data Input Hold Time		t HID	1	_	1		1	_	ns
	Output Valid	CL = 3		_	8.5	_	8.5	_	9	
10	from Clock *1, *2 (tclk = min)	CL = 2	t ac	_	9	_	9	_	10	ns
11	Output in Low-Z		tolz	3	_	3	_	3	_	ns
12	Output in High-Z *3		tонz	3	_	3		3	_	ns
13	Output Hold Time		tон	3	_	3		3	_	ns
14	Time between Refresh		t ref	_	32.8	_	32.8	_	32.8	ms
15	Transition Time		t ⊤	0.5	2	0.5	2	0.5	2	ns
16	Power Down Exit Time		t PDE	3	_	4	_	5	_	ns

(2) BASE VALUES FOR CLOCK COUNT/LATENCY

No.	Parameter	Notes	Symbol	MB8502S064AG -100		MB8502S064AG -84		MB8502S064AG -67		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
1	RAS Cycle Time	*4	t RC	90	_	100	_	110	_	ns
2	RAS Access Time	*5	t rac	_	54	_	56		60	ns
3	CAS Access Time	*6, *9	tcac		24		26		30	ns
4	RAS Precharge Time		t RP	30	_	35	_	40	_	ns
5	RAS Active Time		t RAS	60	100000	65	100000	70	100000	ns
6	RAS to CAS Delay Time	*7	t RCD	30	_	30	_	30	_	ns
7	Write Recovery Time		t wr	10	_	12	_	15	_	ns
8	Write Precharge Time		t RWL	10	_	12	_	15	_	ns
9	RAS to RAS Bank Active Delay Time		t rrd	30	_	30	_	30	_	ns

(3) CLOCK COUNT FORMULA (*8)

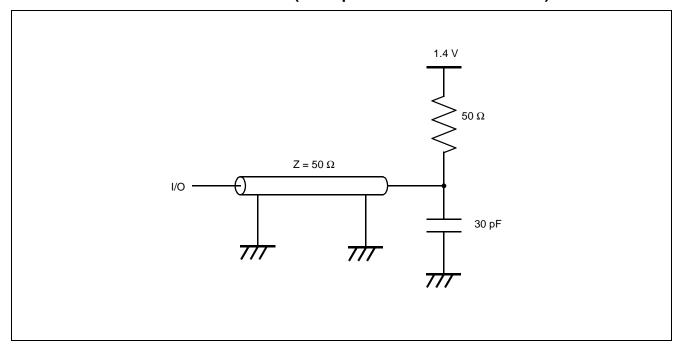
(4) LATENCY (The latency values on these parameters are fixed regardless of clock period.)

No.	Parameter		Symbol	MB8502S064AG -100	MB8502S064AG -84	MB8502S064AG -67	Unit
1	CKE to Clock Disable		Іске	1	1	1	Cycle
2	DQM to Output in High-Z	-	I DQZ	2	2	2	Cycle
3	DQM to Input Data Delay	/	IDQD	0	0	0	Cycle
4	Last Output to Write Command Delay		lowd	2	2	2	Cycle
5	Write Command to Input Data Delay		lowd	0	0	0	Cycle
6	Precharge to	CL = 3	la acc	3	3	3	Cycle
0	Output in High-Z Delay	CL = 2	Iron	2	2	2	Cycle
7	Mode Register Access to Bank Active (min)		I MRD	2	2	2	Cycle
8	CAS to CAS Delay (min)		Іссь	1	1	1	Cycle
9	CAS Bank Delay (min)		Ісво	1	1	1	Cycle

- Notes: *1. Assumes trcd and tcac are satisfied.
 - *2. tac also specifies the access time at burst mode except for first access.
 - *3. Specified where output buffer is no longer driven.
 - *4. Actual clock count of tRC (IRC) will be sum of clock count of tRAS (IRAS) and tRP (IRP).
 - *5. trac is a reference value. Maximum value is obtained from the sum of trac (min) and toac (max).
 - *6. Assumes trac and tac are satisfied.
 - *7. Operation within the trop (min) ensures that trac can be met; if trop is greater than the specified trop (min), access time is determined by teac and tac.
 - *8. All base values are measured from the clock edge at the command input to the clock edge for the next command input.
 - All clock counts are calculated by a simple formula:
 - clock count equals base value divided by clock period (round off to a whole number).
 - *9. The ICAC (CAS latency: CL) is programmed by the mode register.
 - *10. An initial pause (DESL on NOP) of 200 µs is required after power-up followed by a minimum of eight Auto-refresh cycles.
 - *11. 1.4 V or VREF is the reference level for measuring timing of signals. Transition times are measured between V_{IH} (min) and V_{IL} (max).
 - *12. AC characteristics assume $t_T = 1$ ns and 30 pF of capacitive load.

^{*}Source: See MB81117822A Data Sheet for details on the electricals.

■ AC OPERATING TEST CONDITION (Example of AC Test Load Circuit)



■ SERIAL PRESENCE DETECT(SPD) FUNCTION

1. PIN DESCRIPTIONS

SCL (Serial Clock)

SCL input is used to clock all data input/output of SPD

SDA (Serial Data)

SDA is a common pin used for all data input/output of SPD. The SDA pull-up resistor is required due to the open-drain output.

SA₀, SA₁, SA₂ (Address)

Address inputs are used to set the least significant three bits of the eight bits slave address. The address inputs must be fixed to select a particular module and the fixed address of each module must be different each other.

2. SPD OPERATIONS

CLOCK and DATA CONVENTION

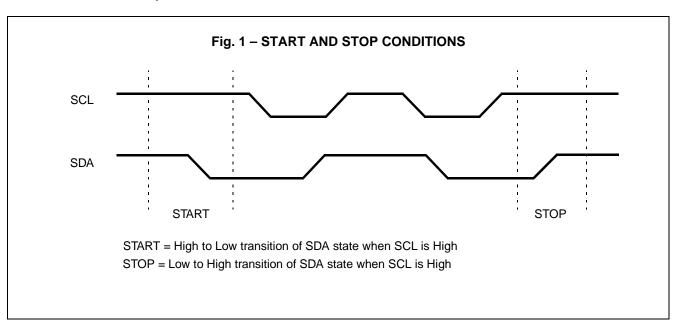
Data states on the SDA can change only during SCL = Low. SDA state changes during SCL = High are indicated start and stop conditions. Refer to Fig. 1 below.

START CONDITION

All commands are preceded by a start condition, which is a transition of SDA state from High to Low when SCL = High. SPD will not respond to any command until this condition has been met.

STOP CONDITION

All read or write operation must be terminated by a stop condition, which is a transition of SDA state from Low to High when SCL = High. The stop condition is also used to make the SPD into the state of standby power mode after a read sequence.



ACKNOWLEDGE

Acknowledge is a software convention used to indicate successful data transfer. The transmitting device, either master or slave, will release the bus after transmitting eight bits. During the ninth clock cycle the receiver will put the SDA line to Low in order to acknowledge that it received the eight bits of data.

The SPD will respond with an acknowledge when it received the start condition followed by slave address issued by master.

In the read operation, the SPD will transmit eight bits of data, release the SDA line and monitor the line for an acknowledge. If an acknowledge is detected and no stop condition is issued by master, the SPD will continue to transmit data. If an acknowledge is not detected, the SPD will terminated further data transmissions. The master must then issue a stop condition to return the SPD to the standby power mode.

In the write operation, upon receipt of eight bits of data the SPD will respond with an acknowledge, and await the next eight bits of data, again responding with an acknowledge until the stop condition is issued by master.

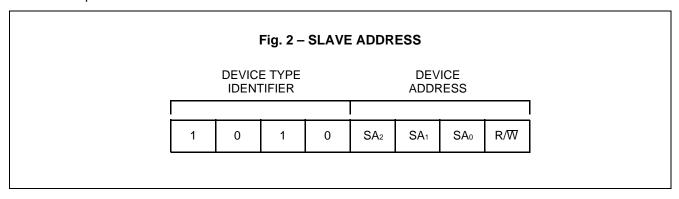
SLAVE ADDRESS ADDRESSING

Following a start condition, the master must output the eight bits slave address. The most significant four bits of the slave address are device type identifier. For the SPD this is fixed as 1010[B]. Refer to the Fig. 2 below.

The next three significant bits are used to select a particular device. A system could have up to eight SPD devices —namely up to eight modules— on the bus. The eight addresses for eight SPD devices are defined by the state of the SA₀, SA₁ and SA₂ inputs.

The last bit of the slave address defines the operation to be performed. When R/\overline{W} bit is "1", a read operation is selected, when R/\overline{W} bit is "0", a write operation is selected.

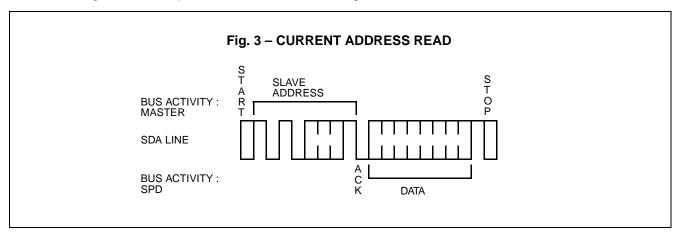
Following the start condition, the SPD monitors the SDA line comparing the slave address being transmitted with its slave address (device type and state of SA_0 , SA_1 , and SA_2 inputs). Upon a correct compare the SPD outputs an acknowledge on the SDA line. Depending on the state of the R/W bit, the SPD will execute a read or write operation.



3. READ OPERATIONS

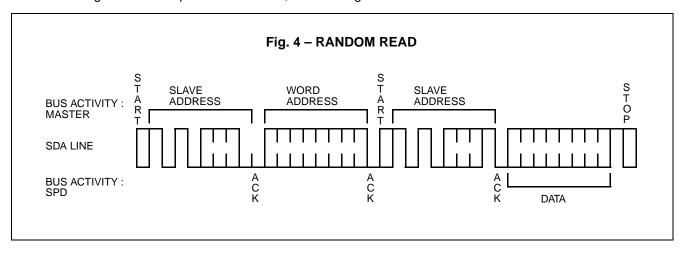
CURRENT ADDRESS READ

Internally the SPD contains an address counter that maintains the address of the last data accessed, incremented by one. Therefore, if the last access (either a read or write operation) was to address(n), the next read operation would access data from address(n+1). Upon receipt of the slave address with the R/W bit = "1", the SPD issues an acknowledge and transmits the eight bits of data during the next eight clock cycles. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 3 for the sequence of address, acknowledge and data transfer.



RANDOM READ

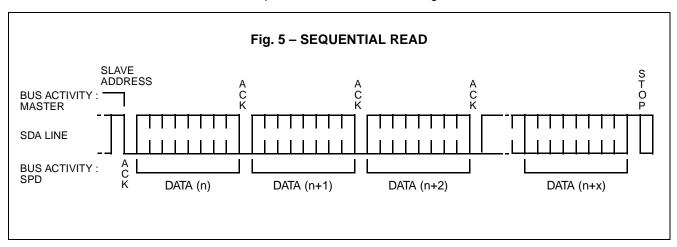
Random Read operations allow the master to access any memory location in a random manner. Prior to issuing the slave address with the R/ \mathbb{W} bit = "1", the master must first perform a "dummy" write operation on the SPD. The master issues the start condition, and the slave address followed by the word address. After the word address acknowledge, the master immediately reissues the start condition and the slave address with the R/ \mathbb{W} bit = "1". This will be followed by an acknowledge from the SPD and then by the eight bits of data. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 4 for the sequence of address, acknowledge and data transfer.



SEQUENTIAL READ

Sequential Read can be initiated as either a current address read or random read. The first data are transmitted as with the other read mode, however, the master now responds with an acknowledge, indicating it requires additional data. The SPD continues to output data for each acknowledge received. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig. 5 for the sequence of address, acknowledge and data transfer.

The data output is sequential, with the data from address(n) followed by the data from address(n+1). The address counter for read operations increments all address bits, allowing the entire memory contents to be serially read during one operation. At the end of the address space (address 255), the counter "rolls over" to address 0 and the SPD continues to output data for each acknowledge received.



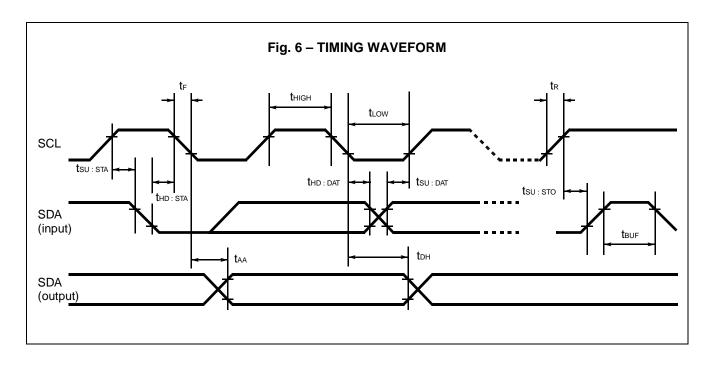
4. DC CHARACTERISTICS

Parameter	Note	Symbol	Condition	Value		Unit
Farameter			Condition	Min.	Max.	Offit
Input Leakage Current		Sili	$0 \text{ V} \leq V_{IN} \leq V_{CC}$	-10	10	μΑ
Output Leakage Current		SILO	0 V ≤ Vout ≤ Vcc	-10	10	μΑ
Output Low Voltage	*1	Svol	IoL = 3.0 mA	_	0.4	V

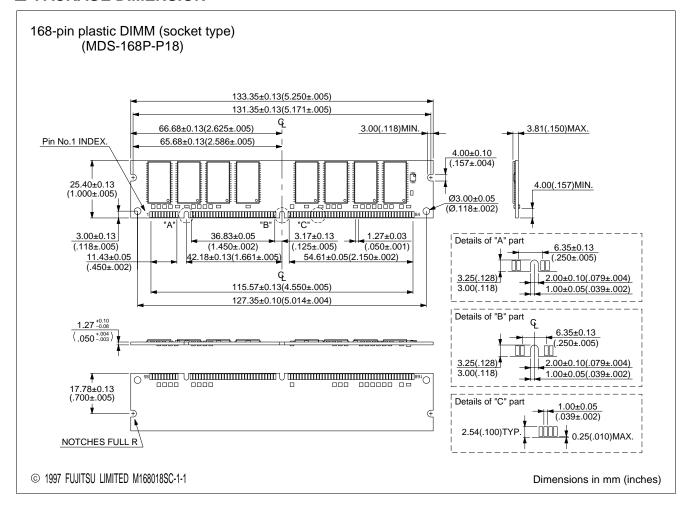
Note: *1. Referenced to Vss.

5. AC CHARACTERISTICS

No.	Parameter	Symbol	Value		l lni4
NO.	Parameter		Min.	Max.	Unit
1	SCL Clock Frequency	fscL	_	100	KHz
2	Noise Suppression Time Constant at SCL, SDA Inputs	Tı	_	100	ns
3	SCL Low to SDA Data Out Valid	t AA	_	3.5	μs
4	Time the Bus Must Be Free Before a New Transmission Can Start	t BUF	4.7	_	μs
5	Start Condition Hold Time	t hd:sta	4.0	_	μs
6	Clock Low Period	tLow	4.7	_	μs
7	Clock High Period	t HIGH	4.0	_	μs
8	Start Condition Setup Time	tsu:sta	4.7	_	μs
9	Data in Hold Time	t HD:DAT	0	_	μs
10	Data in Setup Time	tsu:dat	250	_	ns
11	SDA and SCL Rise Time	t R	_	1	μs
12	SDA and SCL Fall Time	t⊧	_	300	ns
13	Stop Condition Setup Time	t su:sto	4.7	_	μs
14	Data Out Hold Time	tон	100	_	ns
15	Write Cycle Time	t wr	_	15	ms



■ PACKAGE DIMENSION



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